

FAST - (1030640.wsp:1)

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22) (((channel and (narrow or low) adj (bandgap or (

7) (((channel and (narrow or low) adj (bandgap or (

19) (narrow or low) adj (bandgap or (band adj gap))

18) (((narrow or low) adj (bandgap or (band adj gap))

10) (((narrow or low) adj (bandgap or (band adj gap))

10) (((narrow or low) adj (bandgap or (band adj gap))

8) (((narrow or low) adj (bandgap or (band adj gap))

6) (channel near (narrow or low) adj (bandgap or (ba

35) (channel near3 (narrow or low) adj (bandgap or (

54) (source or drain) near3 ((wide\$3 or high) adj (b

2) ((channel near3 (narrow or low) adj (bandgap or (

13) ((source or drain) near3 ((wide\$3 or high) adj (

115) ("SOI" or (insulat\$4 adj substrate)) and ((bar

4) ("SOI" or (insulat\$4 adj substrate)) and ((banc

8) ("SOI" or (insulat\$4 adj substrate)) and ((banc

13) ("5100370" | "5420040" | "5427062") DN

USPAT,US-PGPUB,EPO:JPO,EM,TDB

Default operator: OR

Highlight all hit terms initially

(((small or narrow or low) near3 (bandgap or (band adj gap)) near2 channel)) and (gate and (source and drain) and transistor)) and (substrate and (dielectric or insulat\$4)) and (dielectric near3 constant)

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	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XRef	R	Inventor	S	C
1					US 20040113210 A1	20040617	9	Novel field effect transistor and method of fabrication	257/401	257/188; 257/333; 257/410;		Chau, Robert S. et al.		
2					US 20040099966 A1	20040527	9	Novel field effect transistor and 1/1 method of fabrication				Chau, Robert S. et al.		
3					US 20020185655 A1	20021212	18	Ultra-linear multi-channel field effect transistor	257/192			Fahimulla, Ayub M. et al.		
4					US 5698869 A	19971216	90	Insulated-gate transistor having narrow-bandgap-source	257/192	257/347; 257/616; 257/66;		Yoshimi, Makoto et al.		

Details HTML

Ready

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